MSKSEMI 美森科













ESD

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MOV

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 PLED

2SC4617x-MS

Product specification



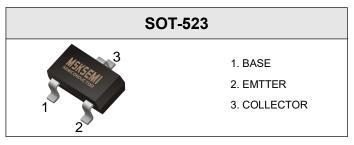


TRANSISTOR (NPN)

Applications

- Low Cob:Cob=2.0pF(Typ)
- Complement to 2SA1774x-MS

Reference News



Marking

2SC4617Q-MS	2SC4617R-MS	2SC4617S-MS		
BQ	BR	BS		

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Value	Unit
Collector-Base Voltage	60	V
Collector-Emitter Voltage	50	V
Emitter-Base Voltage	7	V
Collector Current -Continuous	150	mA
Collector Power Dissipation	150	mW
Operation Junction and Storage Temperature Range	-55-150	$^{\circ}$

ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50uA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l _E =50uA, l _C =0	7			V
Collector cut-off current	Ісво	V _{CB} =60V, I _E =0			0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	lc=50mA, I _B =5mA			0.4	V
Transition frequency	f⊤	V _{CE} =12V, I _C =2mA, f=100MHz		180		MHz
Collector output capacitance	Cob	V _{CB} =12V, I _E =0, f=1MHz			3.5	pF

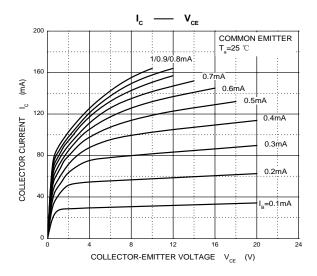
CLASSIFICATION OF hFE

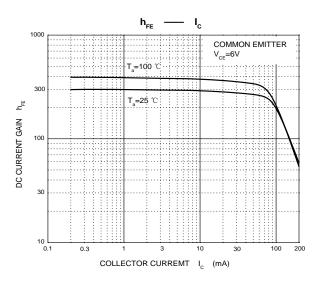
Rank	2SC4617Q-MS	2SC4617R-MS	2SC4617S-MS
Range	120-270	180-390	270-560

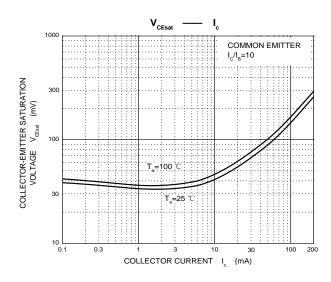


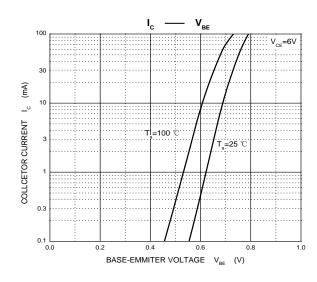
TRANSISTOR (NPN)

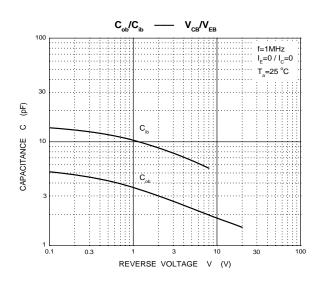
Typical Characteristics

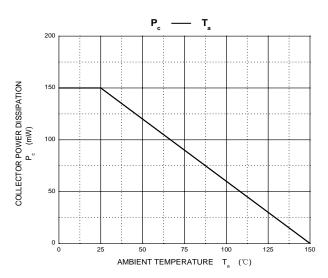








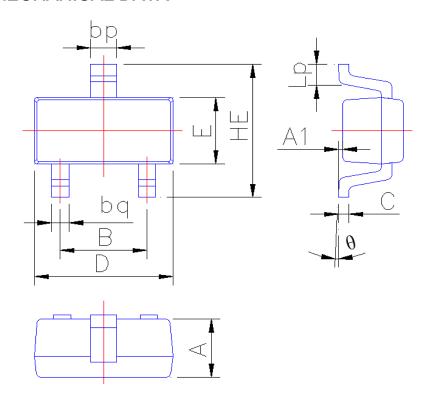






TRANSISTOR (NPN)

PACKAGE MECHANICAL DATA



SOT-523

	Dimension in Millimeters		
Symbol	Min	Max	
Α	0.60	0.80	
A1	0.010	0.100	
В	0.95	1.05	
bp	0.26	0.40	
bq	0.16	0.30	
С	0.09	0.15	
D	1.50	1.70	
E	0.70	0.85	
HE	1.45	1.75	
Lp	0.16	0.36	
θ	0°	5°	

REELSPECIFICATION

P/N	PKG	QTY
2SC4617x-MS	SOT-523	3000





TDANGISTOD (NIDN)

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